

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application.

Listing of Claims:

1. (currently amended) A chamber structure of an inductive coupling plasma etching apparatus, comprising:
 - an etch chamber in which an etching process is performed;
 - a plasma chamber in which plasma is generated; and
 - a segregation wall part having a portion made of ceramic material opposite to the etch chamber, and having a portion made of quartz material opposite to the plasma chamber, the segregation wall part separating the etch chamber from the plasma chamber.
2. (original) The chamber structure of claim 1, wherein the plasma chamber is in an upper portion of the chamber structure, and the etch chamber is in a lower portion of the chamber structure.
3. (original) The chamber structure of claim 1, which is of cylindrical shape.

4. (currently amended) The chamber structure of claim 1, wherein the portion of the segregation wall part opposite to the etch chamber includes a heater that heats the ceramic material portion.
5. (original) The chamber structure of claim 1, wherein the segregation wall part includes gas flow paths and gas exhaust holes that supply process gas into the etch chamber.
6. (currently amended) A chamber structure of an inductive coupling plasma etching apparatus, the chamber structure having cylindrical shape and being divided by one segregation wall part into a first chamber wherein an etching process is performed and a second chamber in which plasma is generated,
the segregation wall part having a portion made of ceramic material that is a ceiling of the first chamber, and having a portion made of quartz material that is a bottom of the second chamber.
7. (original) The chamber structure of claim 6, wherein the portion of the segregation wall part that is a ceiling of the first chamber includes a heater.

8. (original) The chamber structure of claim 6, wherein the segregation wall part includes gas flow paths and gas exhaust holes that supply process gas into the first chamber.

9. (currently amended) A chamber structure of an inductive coupling plasma etching apparatus of cylindrical shape divided into an upper chamber and a lower chamber by one segregation wall part,

the segregation wall part having a portion made of ceramic material that is a ceiling wall of the lower chamber, and having a portion made of quartz material that is a bottom wall of the upper chamber.

10. (original) The chamber structure of claim 9, wherein plasma is generated in the upper chamber.

11. (original) The chamber structure of claim 9, wherein an etching process is performed in the lower chamber.

12. (original) The chamber structure of claim 9, wherein the portion of the segregation wall part that is a ceiling, wall of the lower chamber includes a heater.

13. (original) The chamber structure of claim 9, wherein the segregation wall part includes gas flow paths and gas exhaust holes that supply process gas into the lower chamber.